

# OAI-33 Complex Gate – Domino

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**Group Number: 7**



INDRAPRASTHA INSTITUTE *of*  
INFORMATION TECHNOLOGY  
DELHI

**Group Members :**

- Saksham Gupta – 2019199
- Samaksh Gupta – 2019200
- Shragvi Sidharth Jha – 2019207
- Mihir Chaturvedi– 2019175

# Schematic using XCircuit

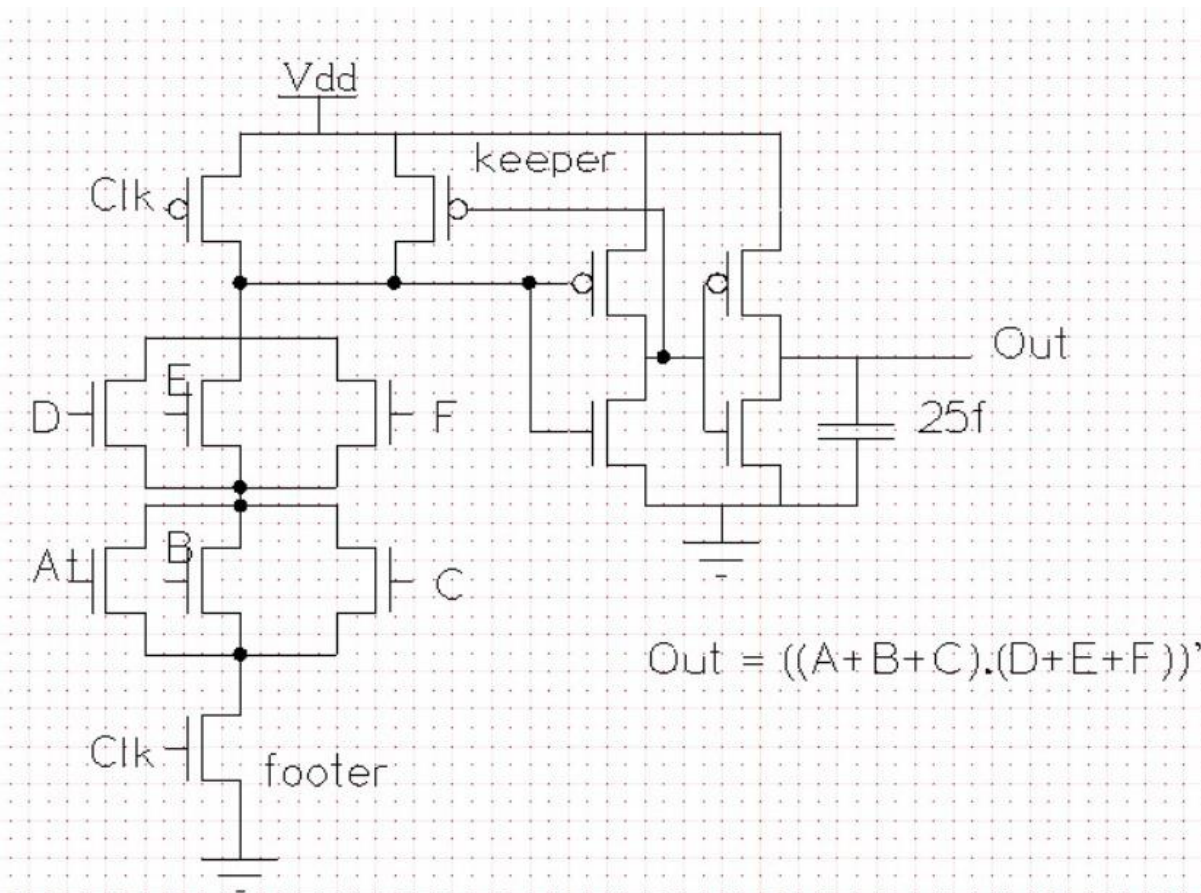


## COMPLEX

Sizing- A, B, C, D, E, F ,clk (footer): 0.405u

clk(precharge): 0.27u, keeper: 0.135u

Inverters- nmos: 0.34u, pmos: 0.68u



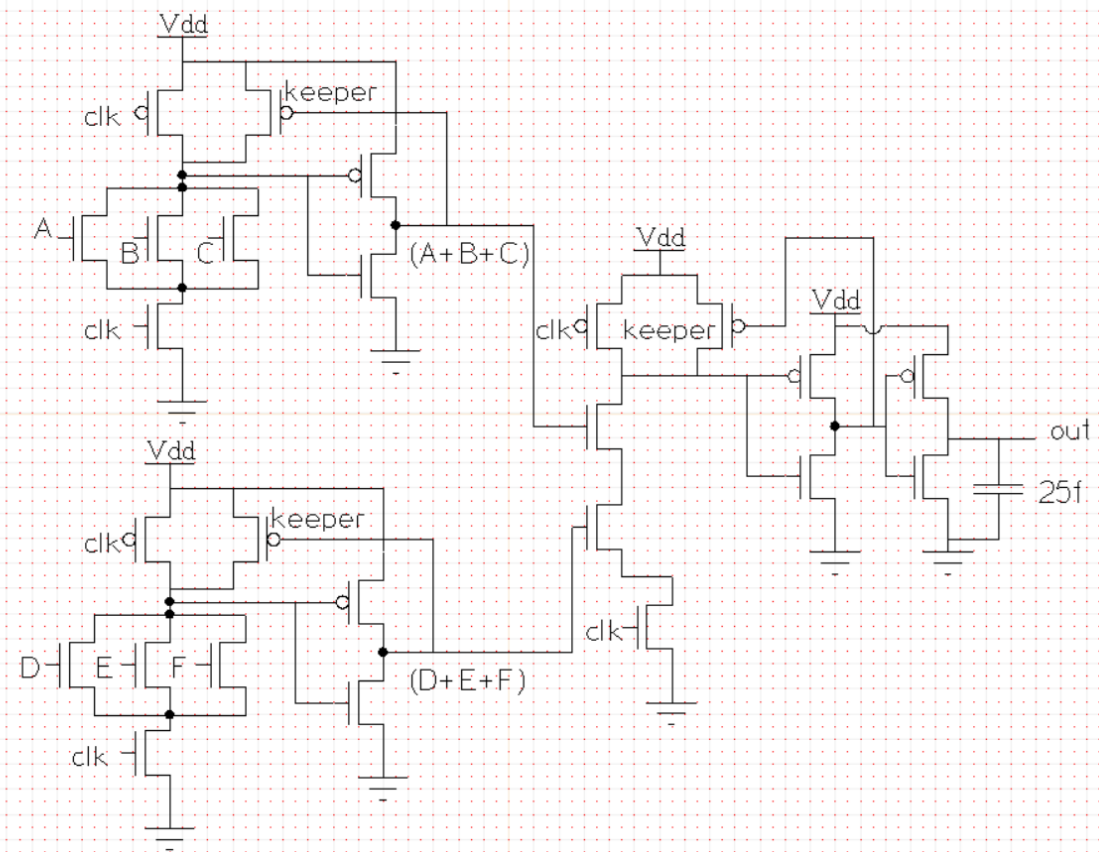
## NON COMPLEX

Sizing- keeper: 0.135u

A, B, C, D, E, F ,clk (footer), clk(precharge), A+B+C(nmos),

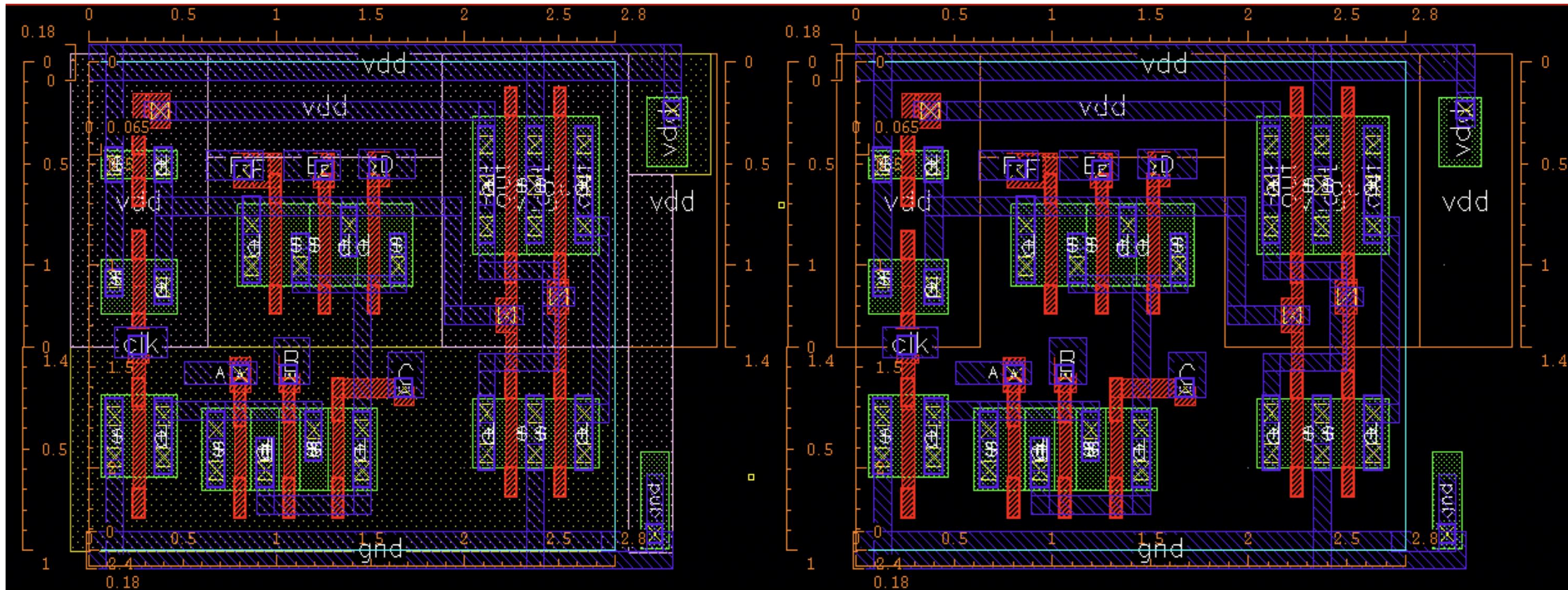
D+E+C(nmos) : 0.405u

Inverters- nmos: 0.34u, pmos: 0.68u





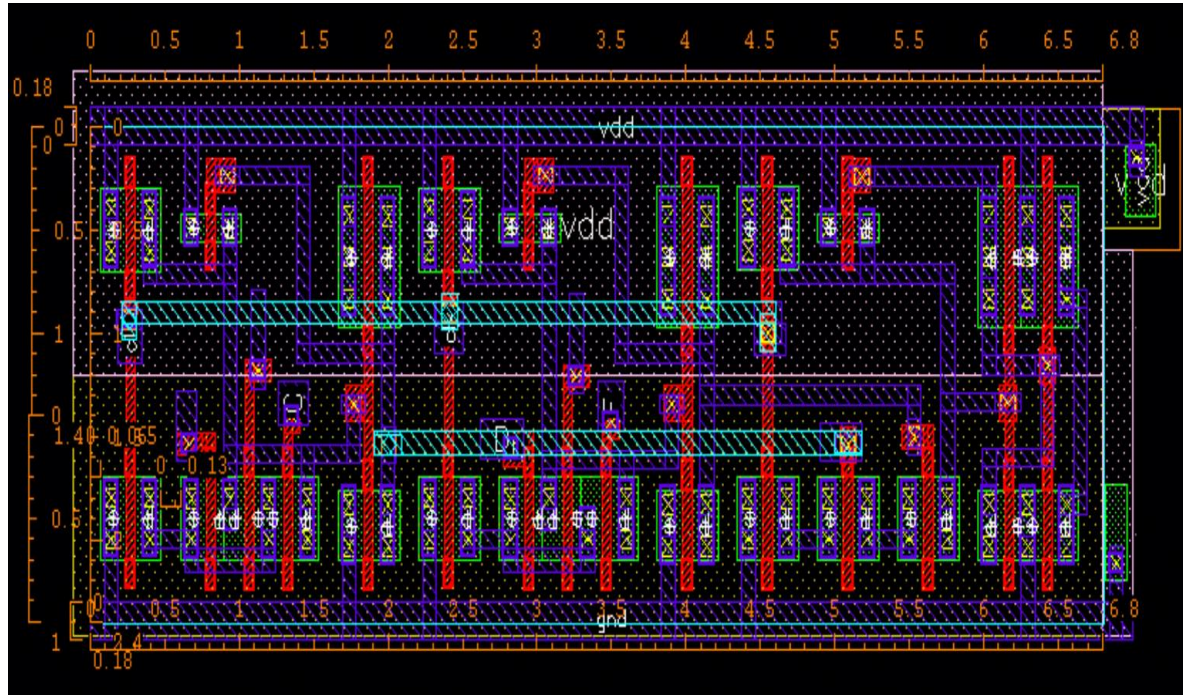
# Layout Screenshots (Complex)



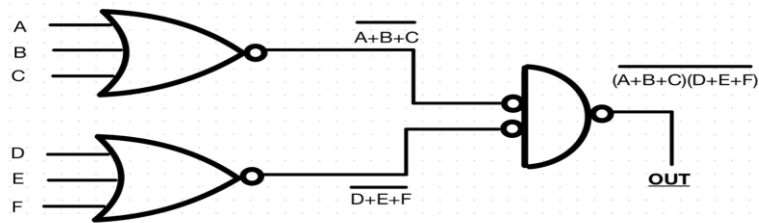
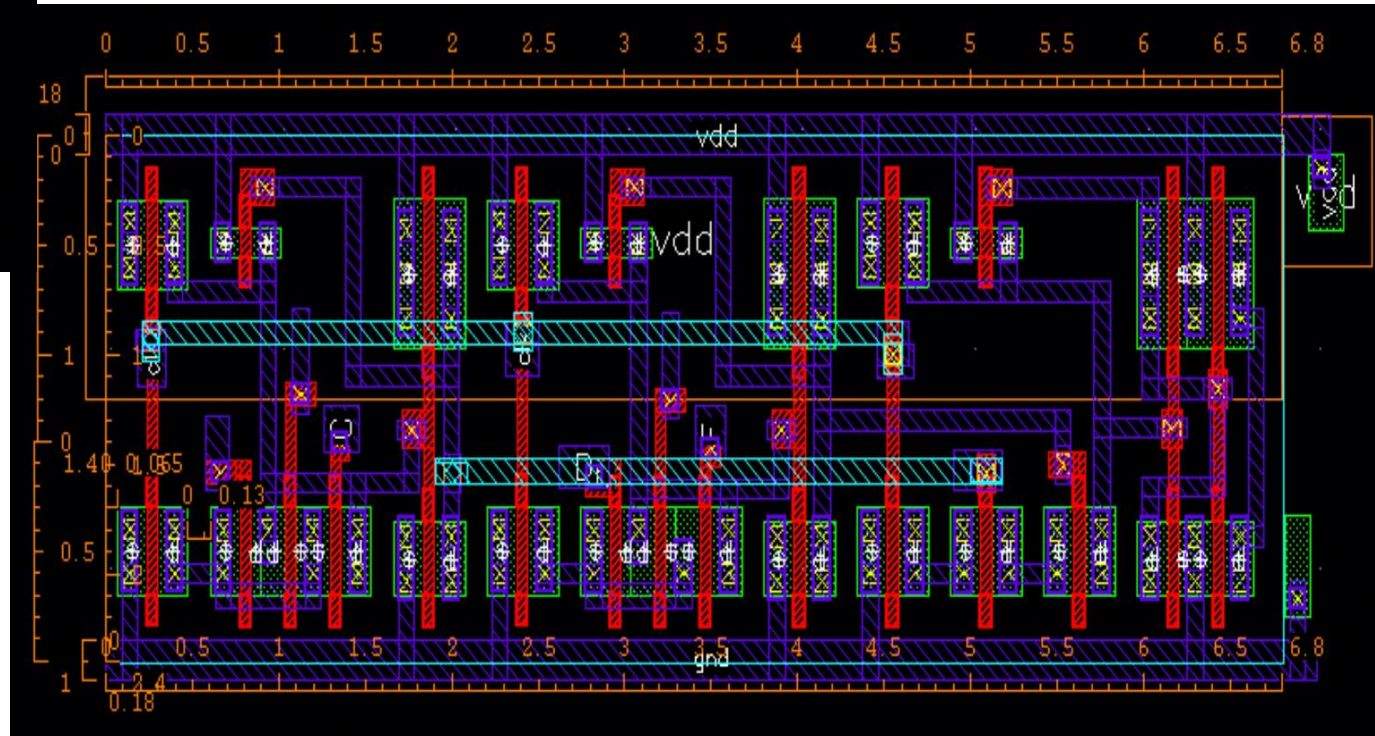
$$\text{Area} = 2.4 * 2.8 = 6.72 \text{ um}^2$$



# Layout Screenshots (Non-Complex)



$$\text{Area} = 2.4 * 6.8 = 16.32 \text{ } \mu\text{m}^2$$

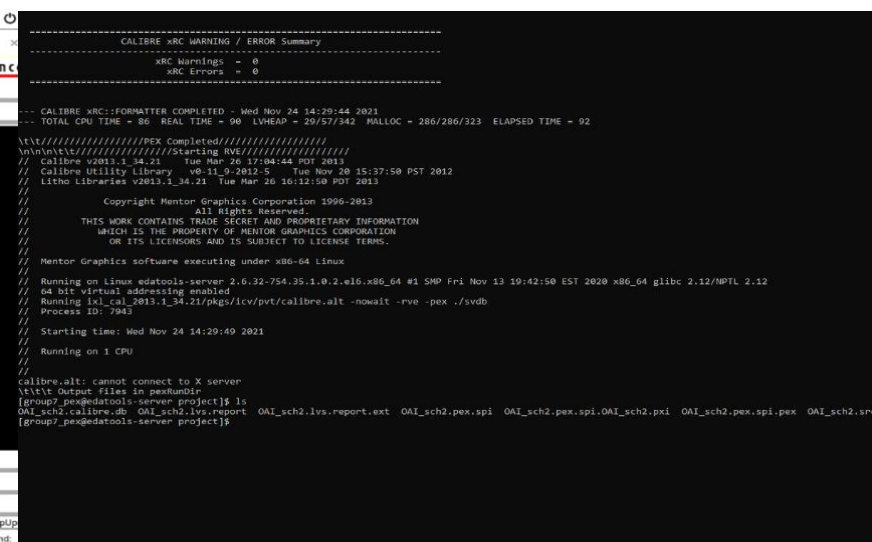
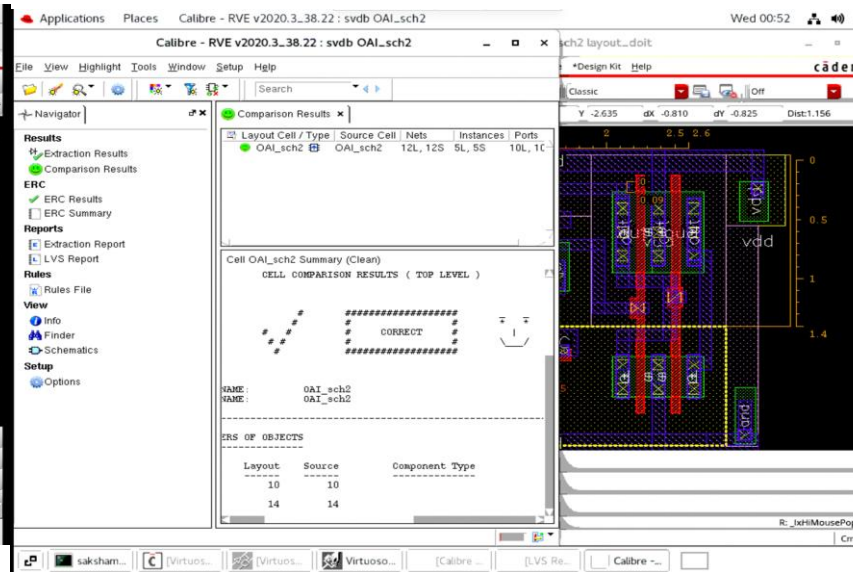
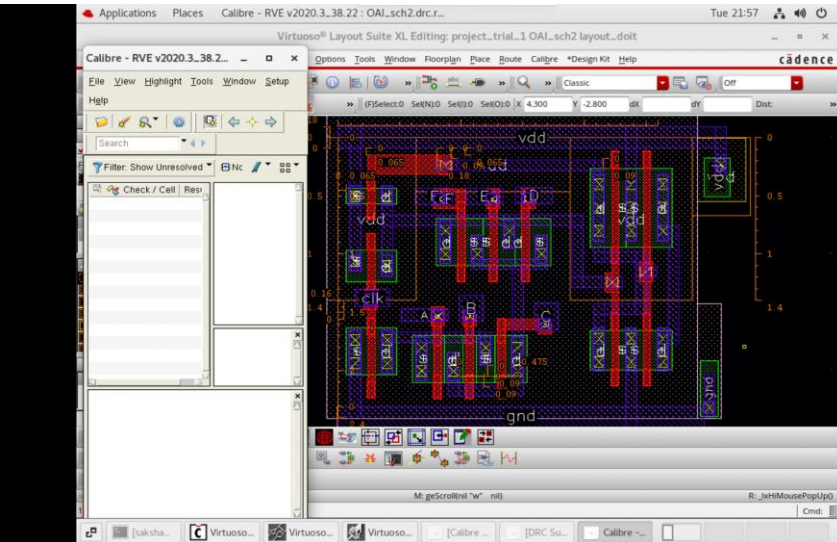




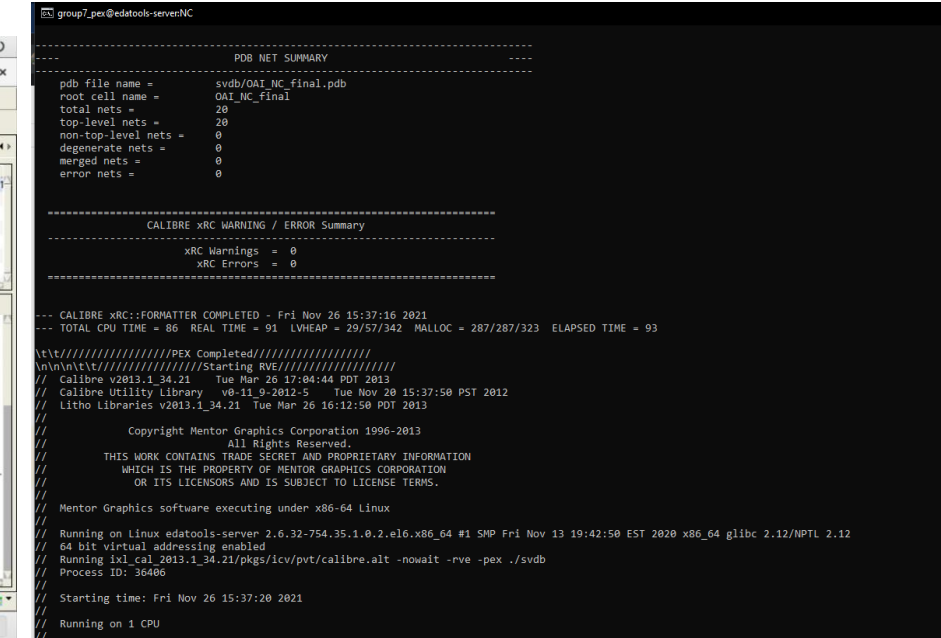
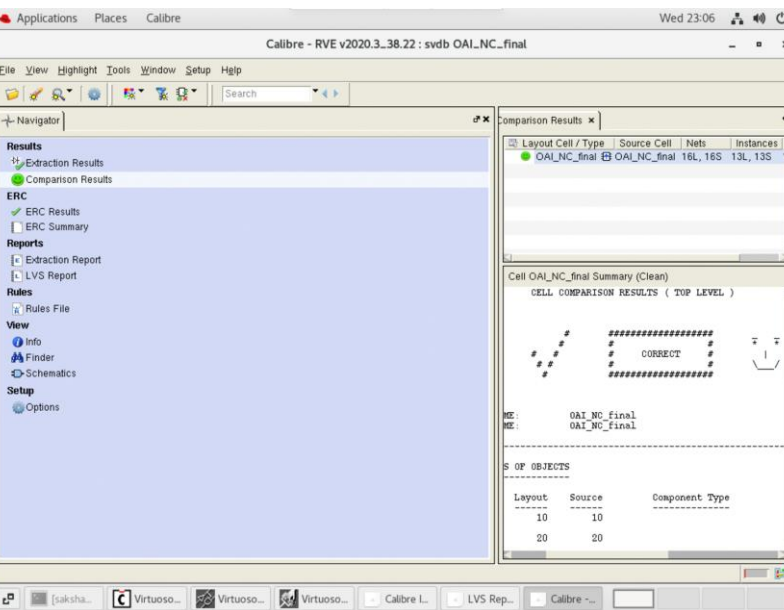
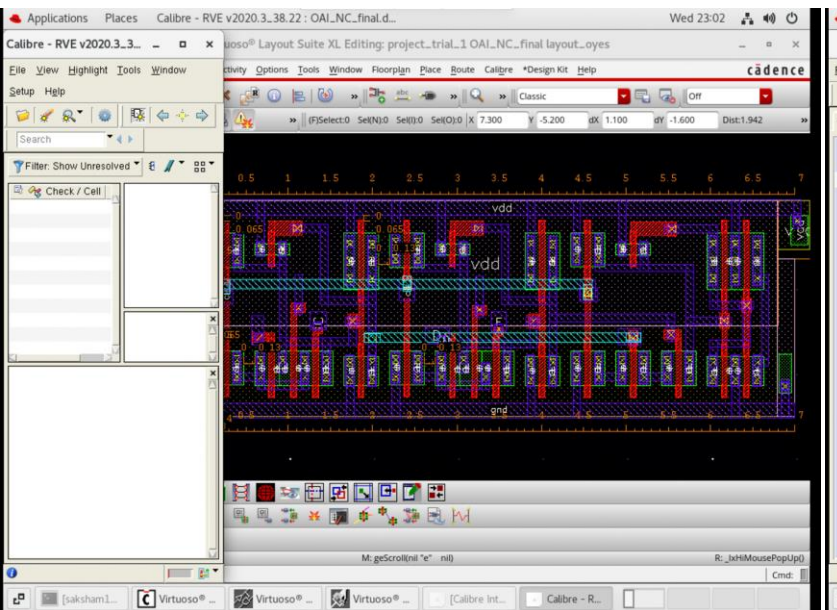
# DRC, LVS, PEX Results



## Complex



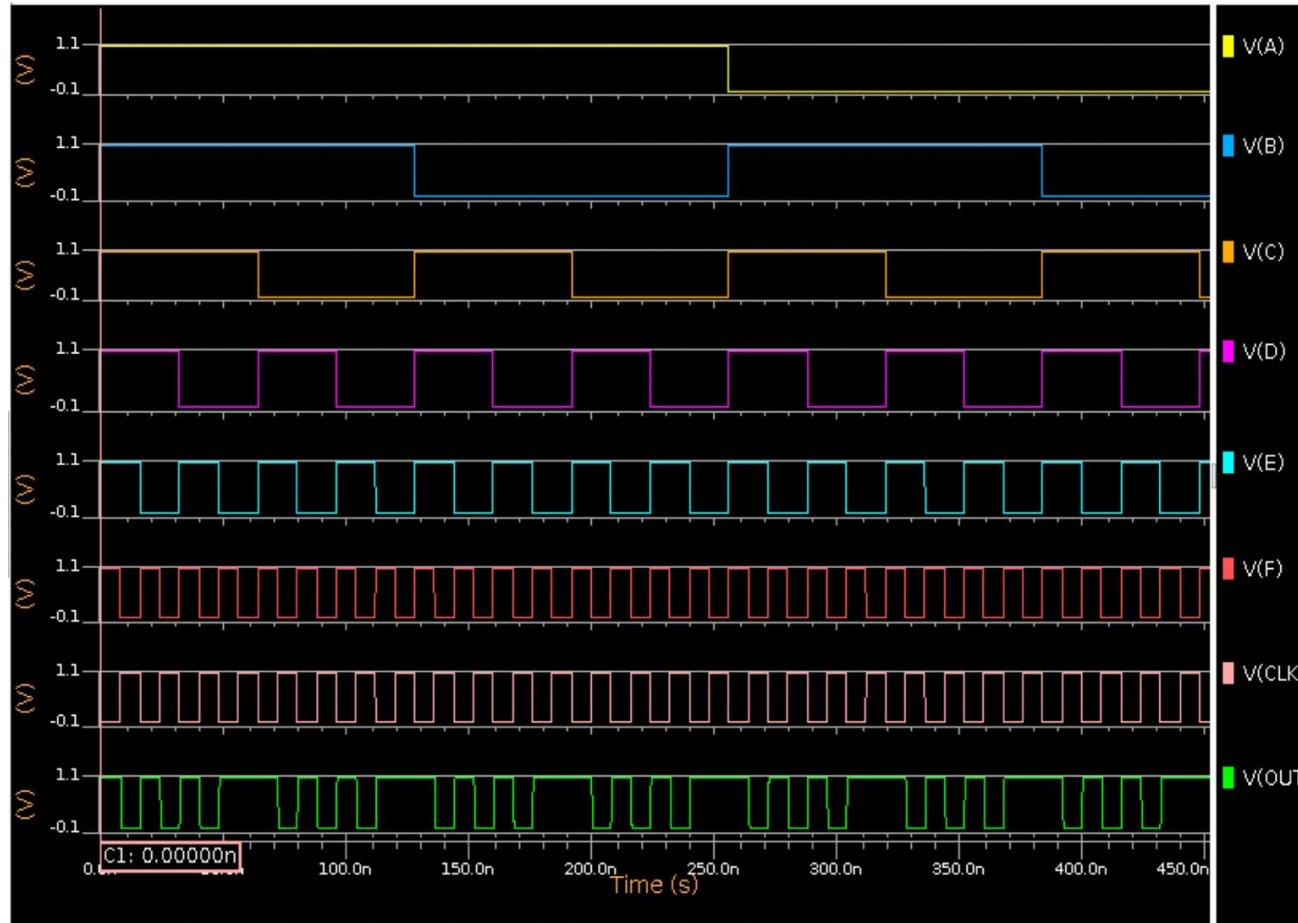
## Non Complex



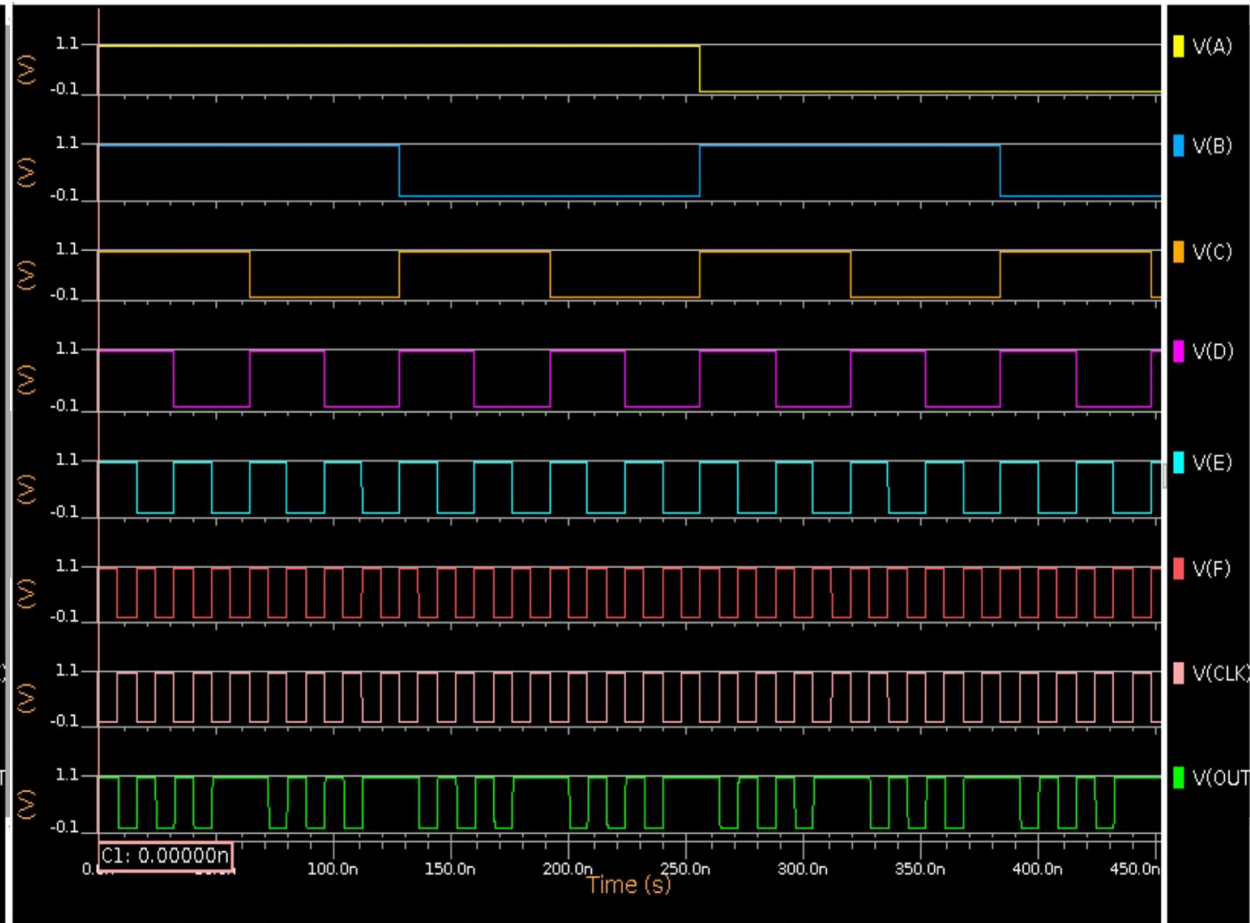
# Simulation Waveforms



Complex



Non Complex



Same waveforms for both Complex and Non Complex Design verifies the functionality.

# Complex-Pre & Post Layout



## RISE AND FALL DELAYS

PVT CORNER ↓	T-fall (Pre-Layout)	T-fall (Post-Layout)	T-rise (Pre-Layout)	T-rise (Post-Layout)
<b>SS, 1.08, 125</b>	0.19676	0.19104	0.18563	0.1857
<b>SS, 1.08, 25</b>	0.17274	0.16806	0.1693	0.16947
<b>SS, 1.08, -40</b>	0.15475	0.15081	0.15409	0.15471
<b>TT, 1.2, 25</b>	0.11789	0.11541	0.12086	0.12134
<b>FF, 1.32, 125</b>	0.099496	0.097815	0.10355	0.10389
<b>FF, 1.32, -40</b>	0.07895	0.077754	0.083116	0.084044

Scale : Nano Seconds

# Complex-Pre & Post Layout



## CONTAMINATION AND PROPAGATION DELAYS

	Pre Condition (A,B,C,D,E,F): (1,1,1,0,0,0) Transition (D,E,F): (0->1)		Pre Condition (A,B,C,D,E,F): (0,0,0,0,0,1) Transition (C): (0->1)	
PVT CORNER	TCD (Pre-Layout)	TCD (Post-Layout)	TPD (Pre-Layout)	TPD (Post-Layout)
SS, 1.08, 125	0.23718	0.25207	0.32044	0.33923
SS, 1.08, 25	0.21462	0.22895	0.28825	0.30708
SS, 1.08, -40	0.19613	0.20946	0.25866	0.27682
TT, 1.2, 25	0.13817	0.14757	0.17409	0.18613
FF, 1.32, 125	0.10944	0.11670	0.13406	0.14322
FF, 1.32, -40	0.091383	0.097378	0.1067	0.11444

Scale : Nano Seconds



# Non Complex-Pre & Post Layout



## RISE AND FALL DELAYS

PVT CORNER	T-fall (Pre-Layout)	T-fall (Post-Layout)	T-rise (Pre-Layout)	T-rise (Post-Layout)
<b>SS, 1.08, 125</b>	<b>0.19673</b>	<b>0.19139</b>	<b>0.18556</b>	<b>0.18528</b>
<b>SS, 1.08, 25</b>	<b>0.1727</b>	<b>0.16833</b>	<b>0.16931</b>	<b>0.16939</b>
<b>SS, 1.08, -40</b>	<b>0.15467</b>	<b>0.15104</b>	<b>0.15399</b>	<b>0.15479</b>
<b>TT, 1.2, 25</b>	<b>0.11788</b>	<b>0.11559</b>	<b>0.12079</b>	<b>0.12135</b>
<b>FF, 1.32, 125</b>	<b>0.099485</b>	<b>0.09799</b>	<b>0.10350</b>	<b>0.10389</b>
<b>FF, 1.32, -40</b>	<b>0.078937</b>	<b>0.07784</b>	<b>0.083098</b>	<b>0.084075</b>

Scale : Nano Seconds

# Non Complex-Pre & Post Layout



## CONTAMINATION AND PROPAGATION DELAYS

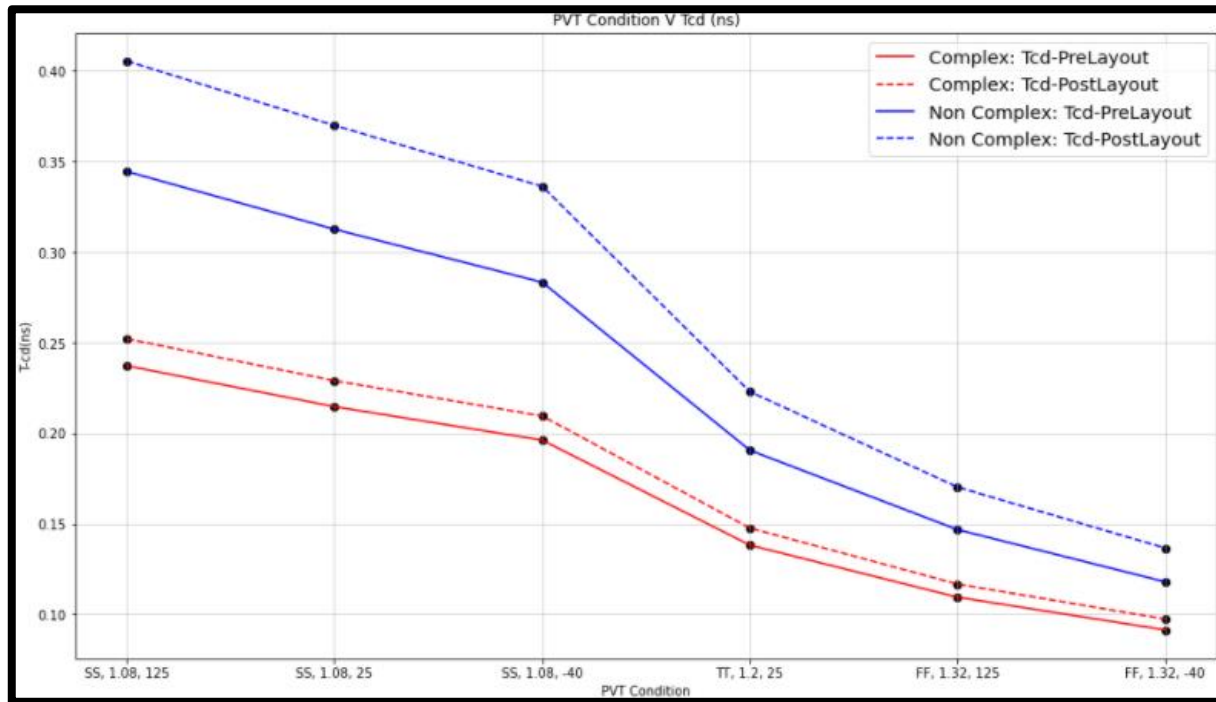
PVT CORNER	TCD (Pre-Layout)	TCD (Post-Layout)	TPD (Pre-Layout)	TPD (Post-Layout)
<b>SS, 1.08, 125</b>	0.3444	0.40539	0.36448	0.42701
<b>SS, 1.08, 25</b>	0.31253	0.36982	0.33064	0.38931
<b>SS, 1.08, -40</b>	0.283283	0.33621	0.29953	0.35364
<b>TT, 1.2, 25</b>	0.19052	0.22288	0.19890	0.23232
<b>FF, 1.32, 125</b>	0.14672	0.17021	0.15198	0.17672
<b>FF, 1.32, -40</b>	0.11792	0.13656	0.12147	0.14106

Scale : Nano Seconds

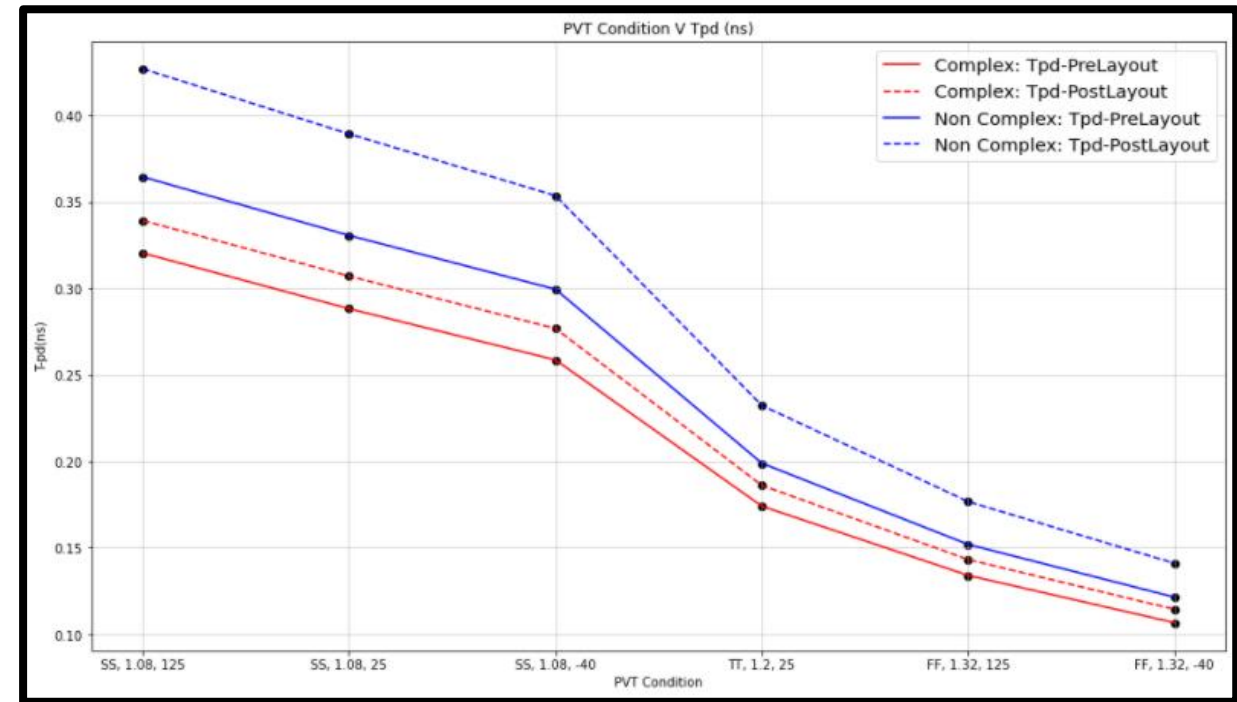
# Delay Graphs



## Contamination Delay



## Propagation Delay





# Complex Vs Non-Complex Design



	COMPLEX	NON COMPLEX	Remark
Number of Transistors	13	25	Increase in 12 transistors.
Area	6.72um <sup>2</sup>	16.32um <sup>2</sup>	2.42 times increase in area for non complex.
T <sub>fall</sub> and T <sub>rise</sub>	SS, 1.08, 125	SS, 1.08, 125	Not much change in T <sub>rise</sub> and T <sub>fall</sub> from complex to non complex
T <sub>cd</sub>	FF, 1.32, -40	FF, 1.32, -40	Contamination delay increased in Non Complex by 16%
T <sub>pd</sub>	SS, 1.08, 125	SS, 1.08, 125	Propagation delay increased in Non Complex by 17%

# Leakage and Power Analysis



FF 1.32 125	COMPLEX		NON COMPLEX	
	Pre Layout	Post Layout	Pre Layout	Post Layout
Leakage	40.267 nA	46.778nA	229.36 nA	245.38 nA
Static Power	53.153 nW	61.74nW	302.76 nW	323.9016nW
Dynamic Power	6.1979 uW	6.557 uW	8.18 uW	8.6414 uW

- **Pre Layout vs Post Layout**
  - Not much change in Leakage and Power between pre and post layout simulations.
- **Complex vs Non Complex**
  - Leakage Current and Static Power increased 5 times from complex to non complex design.
  - Dynamic Power increased by 32% from complex to non complex design.

**Worst PVT Corner: FF, 1.32, 125**

# PPA Analysis & Conclusion

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- We have tried to minimize the area of our design and make a dense layout. Usage of shared diffusion in the nmos for the inputs and bending the nwell from between to accommodate nmos in the p-track region helped us reduce the area.
- We have also used shared diffusion regions for inverter in the domino logic to minimize the area.
- We have considered minimum DRCs wherever possible to reduce the overall horizontal width of our layout which in turn reduces area.
- Non Complex Logic uses more number of transistors and we found the delays increased as moved from complex to non complex designs.
- Complex Design is more power efficient than Non Complex Design.



# ACKNOWLEDGMENT

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*Thank  
You!*



# Work Distribution

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- **Complex Schematic:** Samaksh, Saksham
- **Complex Layout:** Samaksh, Saksham
- **Non Complex Schematic:** Sidharth, Mihir
- **Non Complex Layout:** Saksham, Samaksh, Sidharth
- **Eldo Scripting:** Mihir, Saksham, Samaksh, Sidharth
- **Simulations:** Samaksh, Saksham, Mihir
- **Graphs and Tables:** Sidharth
- **XCircuit and WaveDrom:** Mihir

